

TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

# TLP130

Programmable Controllers  
AC / DC-Input Module  
Telecommunication

The TOSHIBA mini flat coupler TLP130 is a small outline coupler, suitable for surface mount assembly.

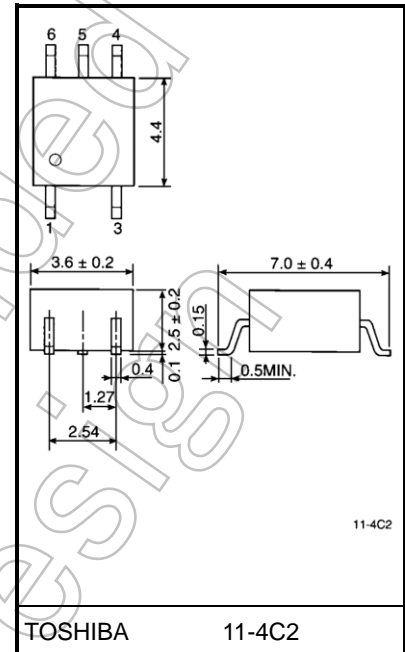
TLP130 consists of a photo transistor, optically coupled to two gallium arsenide infrared emitting diodes connected inverse parallel, and operate directly by AC input current.

- Collector-emitter voltage: 80 V (min)
- Current transfer ratio: 50 % (min)  
Rank GB: 100 % (min)
- Isolation voltage: 3750 Vrms (min)
- UL recognized: UL1577, file no. E67349
- c-UL approved :CSA Component Acceptance Service  
No. 5A, File No.E67349
- Current transfer ratio

Classification	Current Transfer Ratio (%) (I <sub>C</sub> /I <sub>F</sub> )		Marking of Classification
	I <sub>F</sub> = ±5mA, V <sub>CE</sub> = 5V, T <sub>a</sub> = 25°C		
	Min	Max	
Standard	50	600	Blank, GB
Rank GB	100	600	GB

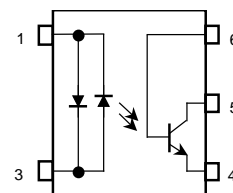
Note: Application type name for certification test, please use standard product type name, i.e. TLP130(GB): TLP130

Unit: mm



Weight: 0.09 g (typ.)

### Pin Configurations (top view)



- 1 : Anode, Cathode
- 3 : Cathode, Anode
- 4 : Emitter
- 5 : Collector
- 6 : Base

Start of commercial production  
1988-04

## Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
LED	Forward current	I <sub>F(RMS)</sub>	50	mA
	Forward current derating (Ta ≥ 53°C)	ΔI <sub>F</sub> /°C	-0.7	mA/°C
	Peak forward current (100 μs pulse, 100pps)	I <sub>FP</sub>	1	A
	Diode power dissipation	P <sub>D</sub>	100	mW
	Diode power dissipation derating (Ta ≥ 53°C)	ΔP <sub>D</sub> /°C	-1.39	mW/°C
	Junction temperature	T <sub>j</sub>	125	°C
Detector	Collector-emitter voltage	V <sub>CEO</sub>	80	V
	Collector-base voltage	V <sub>CBO</sub>	80	V
	Emitter-collector voltage	V <sub>ECO</sub>	7	V
	Emitter-base voltage	V <sub>EBO</sub>	7	V
	Collector current	I <sub>C</sub>	50	mA
	Peak collector current (10 ms pulse, 100 pps)	I <sub>CP</sub>	100	mA
	Power dissipation	P <sub>C</sub>	150	mW
	Power dissipation derating (Ta ≥ 25°C)	ΔP <sub>C</sub> /°C	-1.5	mW/°C
	Junction temperature	T <sub>j</sub>	125	°C
Storage temperature range		T <sub>stg</sub>	-55 to 125	°C
Operating temperature range		T <sub>opr</sub>	-55 to 100	°C
Lead soldering temperature (10 s)		T <sub>sol</sub>	260	°C
Total package power dissipation		P <sub>T</sub>	200	mW
Total package power dissipation derating (Ta ≥ 25°C)		ΔP <sub>T</sub> /°C	-2.0	mW/°C
Isolation voltage (AC, 60 s, R.H. ≤ 60%) (Note 1)		BV <sub>S</sub>	3750	V <sub>rms</sub>

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 1: Device considered a two terminal device: Pins 1 and 3 shorted together and pins 4, 5 and 6 shorted together.

## Recommended Operating Conditions

Characteristic	Symbol	Min	Typ.	Max	Unit
Supply voltage	V <sub>CC</sub>	—	5	48	V
Forward current	I <sub>F(RMS)</sub>	—	16	25	mA
Collector current	I <sub>C</sub>	—	1	10	mA
Operating temperature	T <sub>opr</sub>	-25	—	85	°C

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

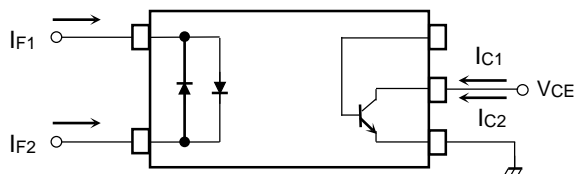
## Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
LED	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = ±10 mA	1.0	1.15	1.3	V
	Capacitance	C <sub>T</sub>	V = 0 V, f = 1 MHz	—	60	—	pF
Detector	Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = 0.5 mA	80	—	—	V
	Emitter-collector breakdown voltage	V <sub>(BR)ECO</sub>	I <sub>E</sub> = 0.1 mA	7	—	—	V
	Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = 0.1 mA	80	—	—	V
	Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = 0.1 mA	7	—	—	V
	Collector dark current	I <sub>CEO</sub>	V <sub>CE</sub> = 48 V	—	10	100	nA
				V <sub>CE</sub> = 48 V, Ta = 85°C	—	2	50
	Collector dark current	I <sub>CER</sub>	V <sub>CE</sub> = 48 V, Ta = 85°C R <sub>BE</sub> = 1 MΩ	—	0.5	10	μA
	Collector dark current	I <sub>CBO</sub>	V <sub>CB</sub> = 10 V	—	0.1	—	nA
	DC forward current gain	h <sub>FE</sub>	V <sub>CE</sub> = 5 V, I <sub>C</sub> = 0.5 mA	—	400	—	—
	Capacitance collector to emitter	C <sub>CE</sub>	V = 0 V, f = 1 MHz	—	10	—	pF

## Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Current transfer ratio	I <sub>C</sub> /I <sub>F</sub>	I <sub>F</sub> = ±5mA, V <sub>CE</sub> = 5V Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	I <sub>C</sub> /I <sub>F(sat)</sub>	I <sub>F</sub> = ±1mA, V <sub>CE</sub> = 0.4V Rank GB	—	60	—	%
			30	—	—	
Base photo-current	I <sub>PB</sub>	I <sub>F</sub> = ±5mA, V <sub>CB</sub> = 5V	—	10	—	μA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = 2.4mA, I <sub>F</sub> = ±8mA	—	—	0.4	V
		I <sub>C</sub> = 0.2mA, I <sub>F</sub> = ±1mA	—	0.2	—	
		Rank GB	—	—	0.4	
Off-state collector current	I <sub>C(off)</sub>	I <sub>F</sub> = ±0.7mA, V <sub>CE</sub> = 48V	—	1	10	μA
CTR symmetry	I <sub>C(ratio)</sub>	I <sub>C</sub> (I <sub>F</sub> = -5mA) / I <sub>C</sub> (I <sub>F</sub> = 5mA) (Note 1)	0.33	—	3	—

Note 1: 
$$I_{C(ratio)} = \frac{I_{C2}(I_F = I_{F2}, V_{CE} = 5V)}{I_{C1}(I_F = I_{F1}, V_{CE} = 5V)}$$



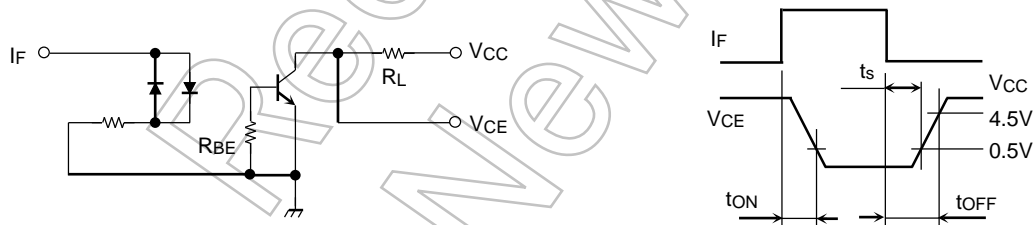
**Isolation Characteristics (Ta = 25°C)**

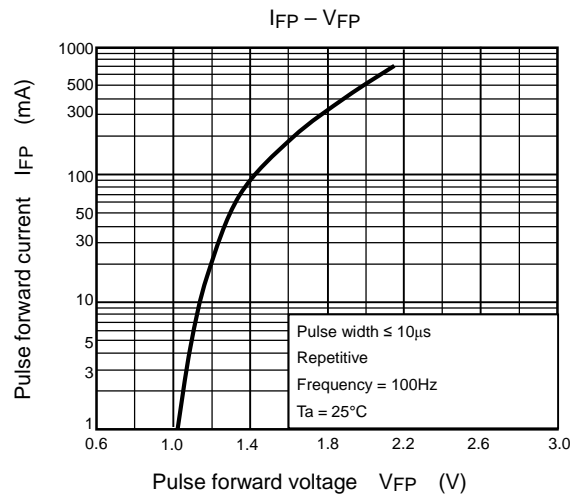
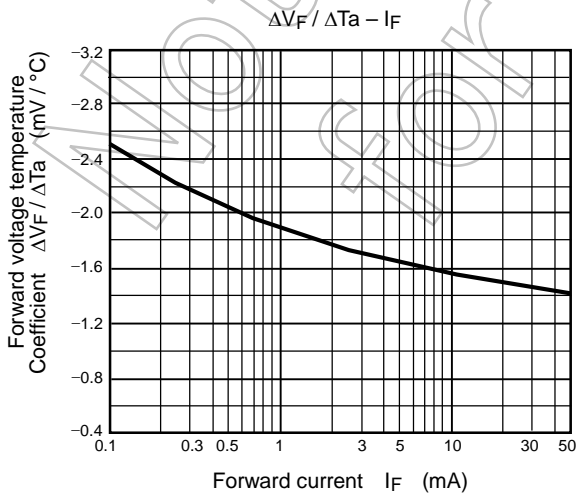
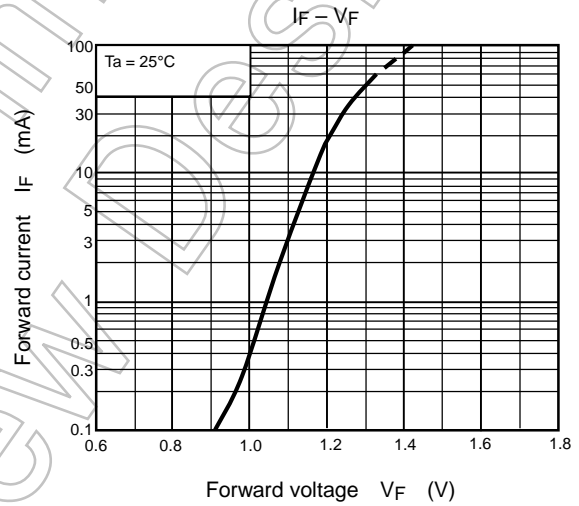
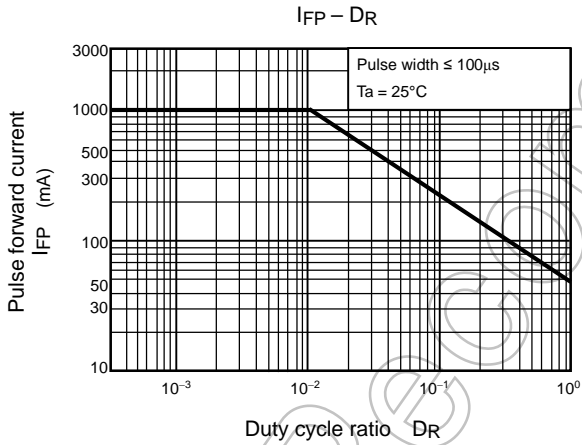
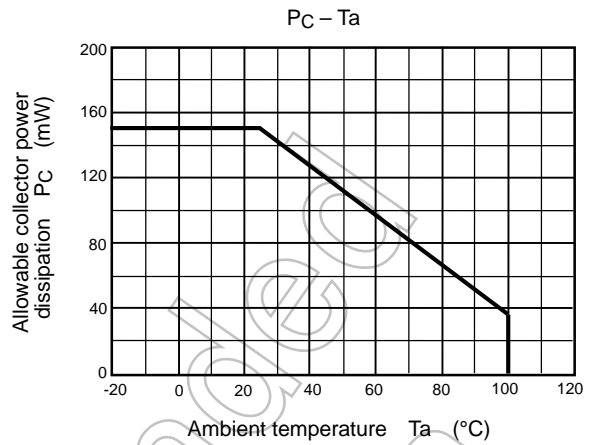
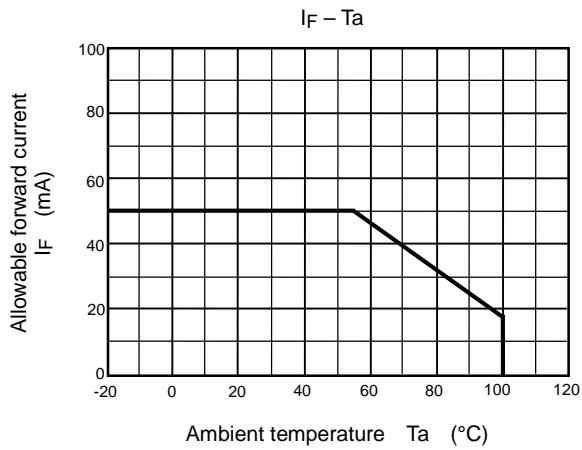
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Capacitance input to output	Cs	V <sub>S</sub> = 0 V, f = 1MHz	—	0.8	—	pF
Isolation resistance	R <sub>S</sub>	V <sub>S</sub> = 500 V, R.H. ≤ 60%	5×10 <sup>10</sup>	10 <sup>14</sup>	—	Ω
Isolation voltage	BV <sub>S</sub>	AC, 60 s	3750	—	—	V <sub>rms</sub>
		AC, 1 s, in oil	—	10000	—	
		DC, 60 s, in oil	—	10000	—	V <sub>dc</sub>

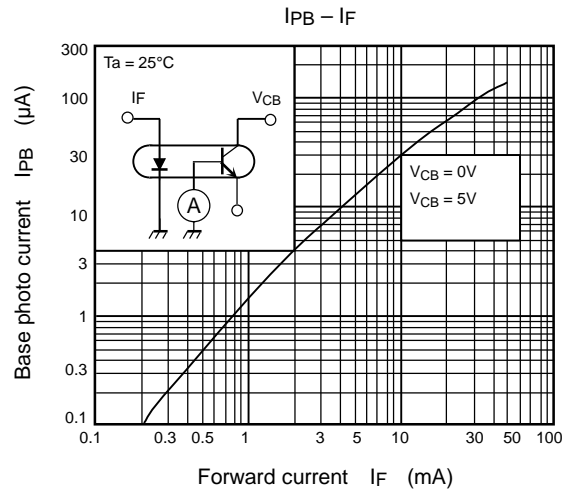
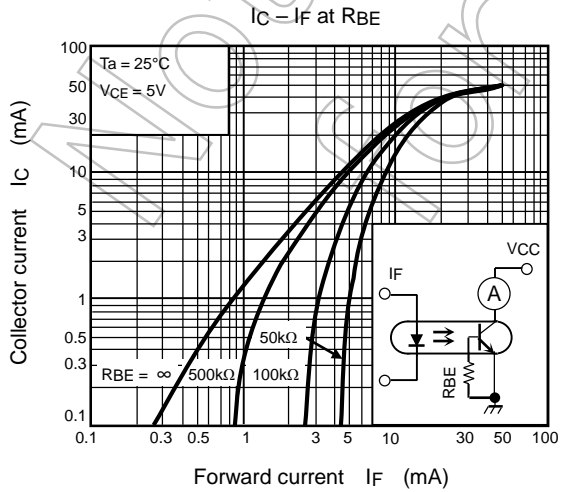
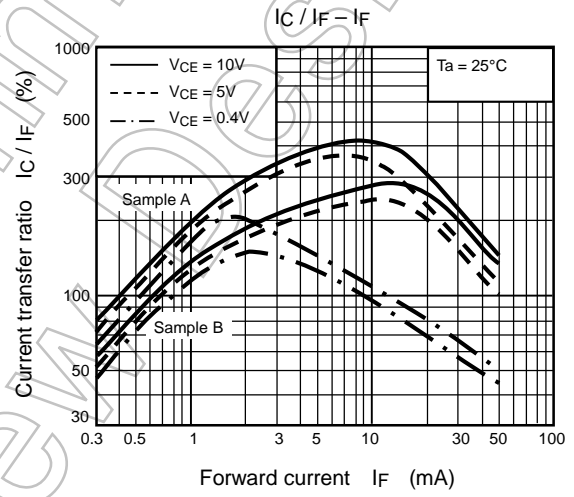
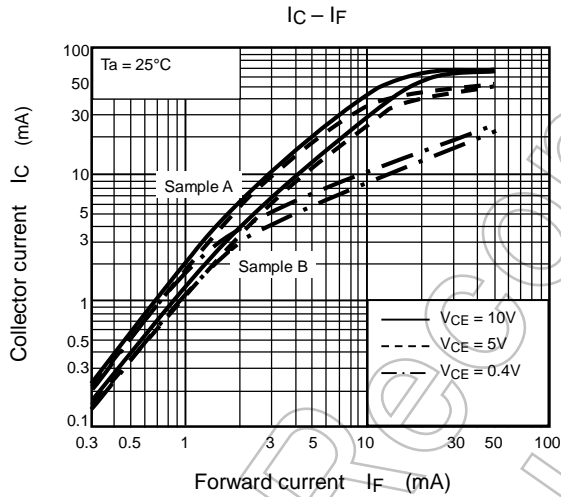
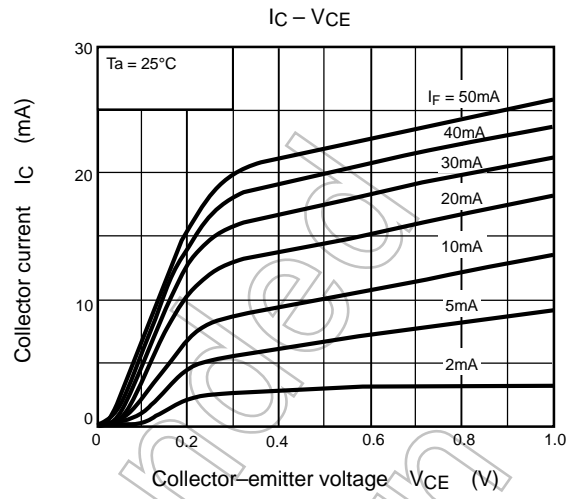
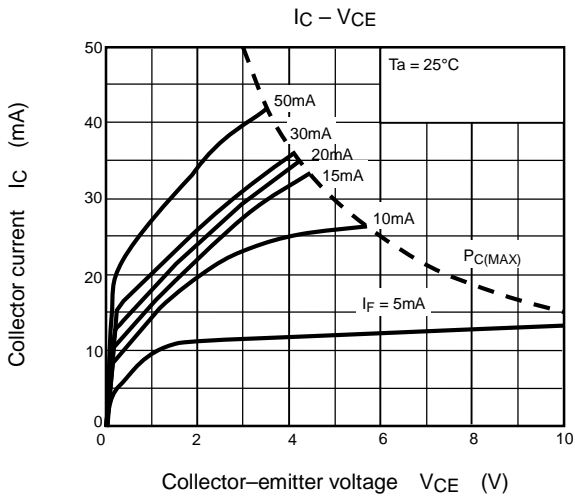
**Switching Characteristics (Ta = 25°C)**

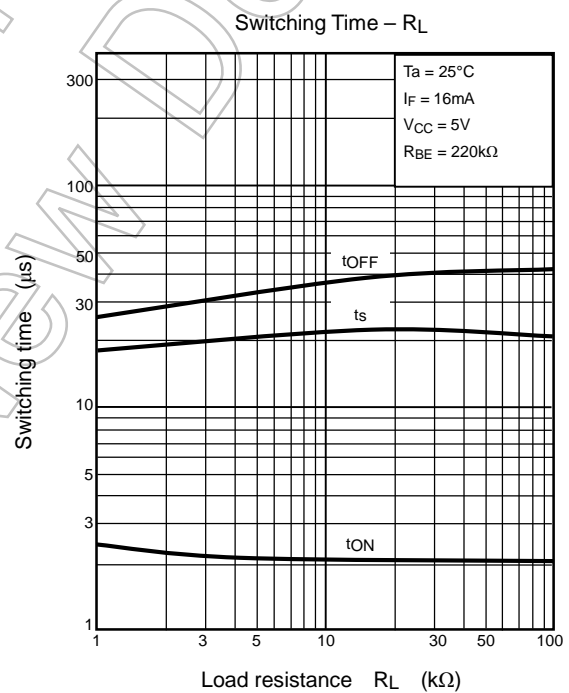
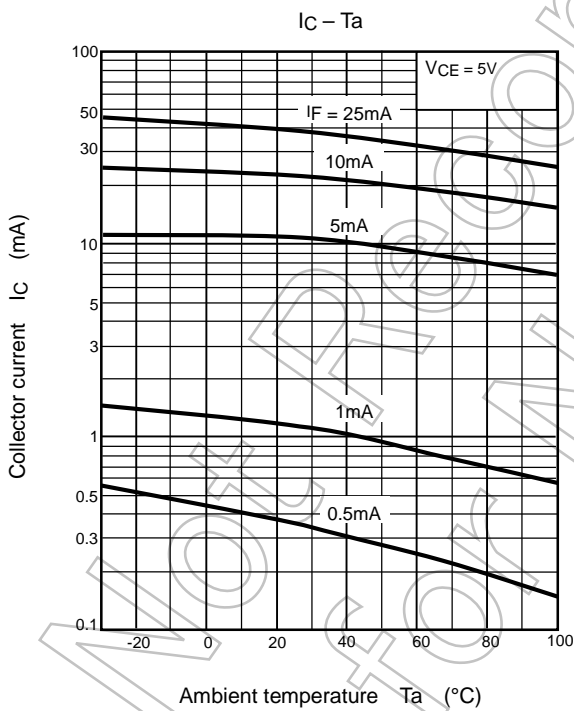
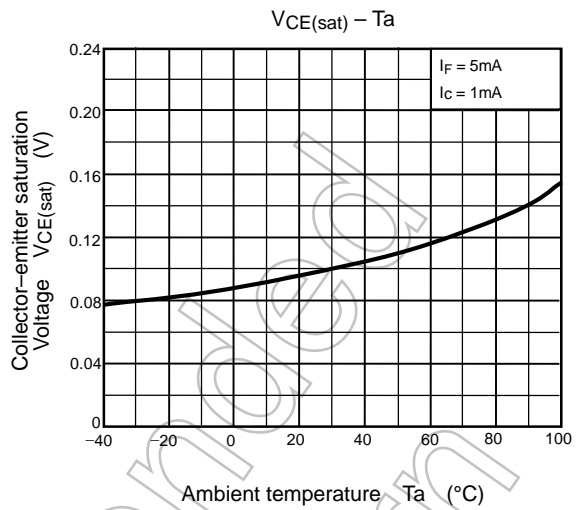
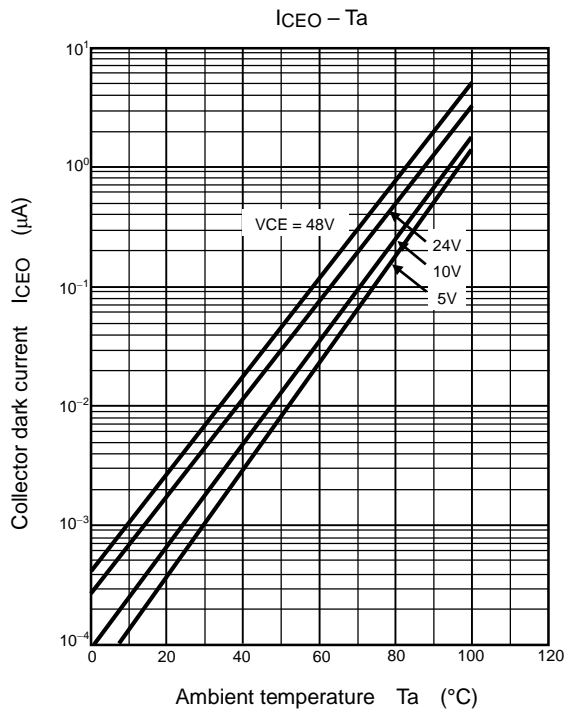
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit
Rise time	t <sub>r</sub>	V <sub>CC</sub> = 10 V, I <sub>C</sub> = 2 mA R <sub>L</sub> = 100 Ω	—	2	—	μs
Fall time	t <sub>f</sub>		—	3	—	
Turn-on time	t <sub>on</sub>		—	3	—	
Turn-off time	t <sub>off</sub>		—	3	—	
Turn-on time	t <sub>ON</sub>	R <sub>L</sub> = 1.9 kΩ (Fig.1)	—	2	—	μs
Storage time	t <sub>s</sub>	R <sub>BE</sub> = OPEN	—	25	—	
Turn-off time	t <sub>OFF</sub>	V <sub>CC</sub> = 5 V, I <sub>F</sub> = ±16 mA	—	40	—	
Turn-on time	t <sub>ON</sub>	R <sub>L</sub> = 1.9 kΩ (Fig.1)	—	2	—	
Storage time	t <sub>s</sub>	R <sub>BE</sub> = 220 kΩ	—	20	—	μs
Turn-off time	t <sub>OFF</sub>	V <sub>CC</sub> = 5 V, I <sub>F</sub> = ±16 mA	—	30	—	

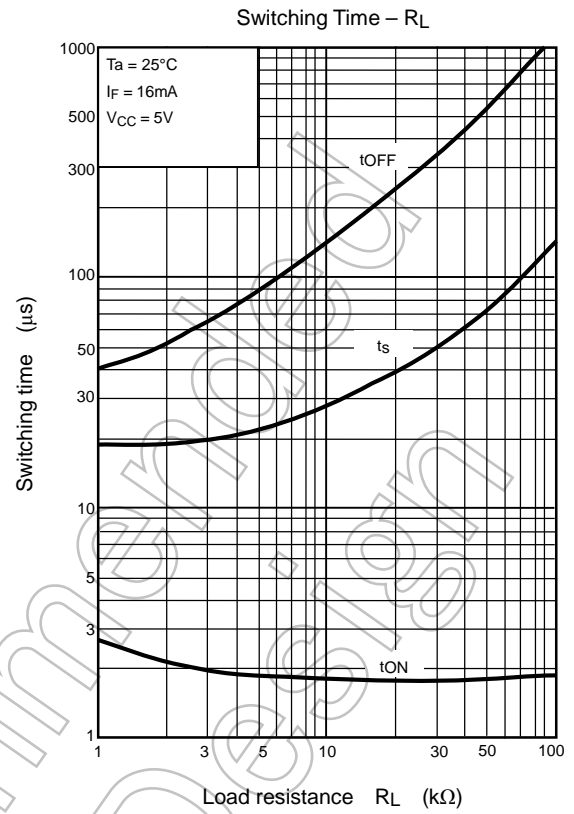
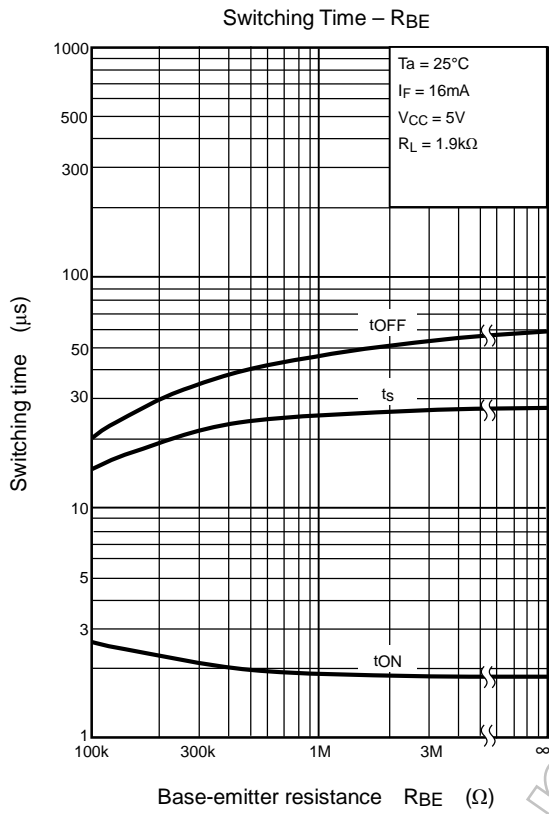
Fig. 1 Switching time test circuit











Not Recommended for New Design

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